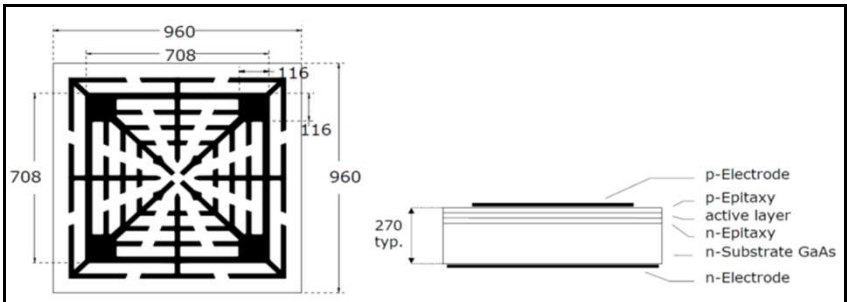
EPIGAP Optronic GmbH
Koepenicker Str. 325b
D-12555 Berlin
Fon: +49 (0)30 657637 60
Fax: +49 (0)30 657637 70
sales@epigap-optronic.de

Data Sheet

LED Chip Infrared EOLC-980-11

Rev. 03, 2017

Radiation	Type	Electrodes
Infrared	AlGaAs/GaAs, MQW	P (anode) up



typ. dimensions

typ thickness: 190±40 µm

anode: gold alloy, 1.5 µm

cathode: gold alloy, 0.5 µm
structured, 25% covered

Optical and Electrical Characteristics

T_{amb}= 25°C, unless otherwise specified

Parameter	Test cond.	Symbol	Min	Typ	Max	Unit
Forward voltage	I_F=100 mA	V_F		1.25		V
Forward voltage	I_F=350 mA	V_F		1.30		V
Reverse current	I_R=5 V	I_R			10	µA
Radiant power*	I_F=50 mA	Φ_e		4.5		mW
Radiant intensity*	I_F=350 mA	I_e		5		mW/sr
Peak wavelength	I_F=350 mA	λ_p		980		nm
FWHM	I_F=350 mA	$\lambda_{0.5}$		40		nm
Switching times	I_F=350 mA	t_r, t_f		20		ns

*Measured on bare chip on TO-18 header

Packing

Chips on adhesive film with wire bond side up

Art. No. 113 014

RoHS COMPLIANT Pb Pb-Free